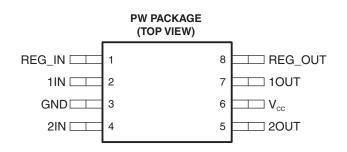


DUAL HIGH-SPEED MOSFET DRIVER

Check for Samples: TPS2811-Q1

FEATURES

- Qualified for Automotive Applications
- Industry-Standard Driver Replacement
- 25-ns Max Rise/Fall Times and 40-ns Max
 Propagation Delay With 1-nF Load, V_{CC} = 14 V
- 2-A Peak Output Current, V_{CC} = 14 V
- 5-µA Supply Current With Input High or Low
- 4-V to 14-V Supply-Voltage Range; Internal Regulator Extends Range to 40 V
- -40°C to 125°C Ambient-Temperature Operating Range



DESCRIPTION

The TPS2811 dual high-speed MOSFET driver is capable of delivering peak currents of 2 A into highly capacitive loads. This performance is achieved with a design that inherently minimizes shoot-through current and consumes an order of magnitude less supply current than competitive products.

The TPS2811 driver include a regulator to allow operation with supply inputs between 14 V and 40 V. The regulator output can power other circuitry, provided power dissipation does not exceed package limitations. When the regulator is not required, REG_IN and REG_OUT can be left disconnected or both can be connected to V_{CC} or GND.

TPS2811 driver is available in an 8-pin TSSOP package and operates over a ambient temperature range of -40°C to 125°C.

ORDERING INFORMATION(1)

T _A	PACKAGE ⁽²⁾		ORDERABLE PART NUMBER	TOP-SIDE MARKING	
-40°C to 125°C	TSSOP – PW	Reel of 2000	TPS2811QPWRQ1	2811Q	

For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI
web site at www.ti.com.

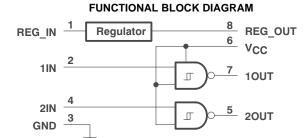
(2) Package drawings, thermal data, and symbolization are available at www.ti.com/packaging.

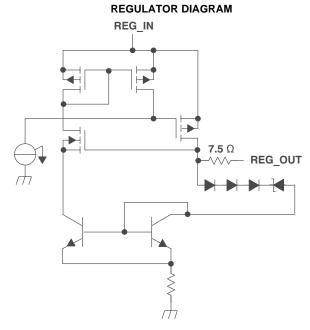


Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

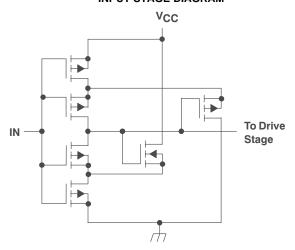
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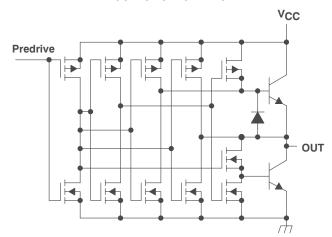




INPUT STAGE DIAGRAM



OUTPUT STAGE DIAGRAM



TERMINAL FUNCTIONS

TE	ERMINAL	DECODIDATION
NAME	NO.	DESCRIPTION
REG_IN	1	Regulator input
1IN	2	Input 1
GND	3	Ground
2IN	4	Input 2
2OUT	5	Output 2; 2OUT = 2IN
V _{CC}	6	Supply voltage
1OUT	7	Output 1; 10UT = 1IN
REG_OUT	8	Regulator output



ABSOLUTE MAXIMUM RATINGS(1)(2)

over operating free-air temperature range (unless otherwise noted)

V_{CC}	Supply voltage	-0.3 V to 15 V	
	Regulator input voltage range	REG_IN	VCC -0.3 V to 42 V
	Input voltage range	1IN, 2IN	-0.3 V to VCC +0.5 V
	Output voltage range	10UT, 20UT	-0.5 < V < VCC +0.5 V
	Continuous regulator output current	REG_OUT	25 mA
	Continuous output current	10UT, 20UT	±100 mA
T _A	Operating ambient temperature range		-40°C to 125°C
T _{stg}	Storage temperature range		-65°C to 150°C

⁽¹⁾ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

RECOMMENDED OPERATING CONDITIONS

				MIN	MAX	UNIT
	Regulator input voltage			8	40	V
V_{CC}	Supply voltage				14	V
	Input voltage	1IN, 2IN		-0.3	V_{CC}	V
	Continuous regulator output current	REG_OUT		0	20	mA
T _A	Operating ambient temperature range	· · · · · · · · · · · · · · · · · · ·		-40	125	ů

ELECTRICAL CHARACTERISTICS

over recommended operating ambient temperature range, $V_{CC} = 10 \text{ V}$, REG_IN open, $C_L = 1 \text{ nF}$ (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT
INPU	тѕ	·				
		V _{CC} = 5 V		3.3	4	
V_{T+}	Positive-going input threshold voltage	V _{CC} = 10 V		5.8	9	V
		V _{CC} = 14 V		8.3	13	
		$V_{CC} = 5 V$	1	1.6		
$V_{T_{-}}$	Negative-going input threshold voltage	V _{CC} = 10 V	1	4.2		V
		V _{CC} = 14 V	1	6.2		
	Input hysteresis	$V_{CC} = 5 V$		1.6		V
I _I	Input current	Inputs = 0 V or V_{CC}	-1	0.2	1	μΑ
CI	Input capacitance			5	10	pF
OUTF	PUTS					
\/	Lligh lovel output voltage	$I_O = -1 \text{ mA}$	9.75	9.9		V
V _{OH}	High-level output voltage	I _O = −100 mA	8	9.1		V
\/	Low level output valtage	I _O = 1 mA		0.18	0.25	V
V _{OL}	Low-level output voltage	I _O = 100 mA		1	2	V
Io	Peak output current	V _{CC} = 10 V		2		Α
REGU	JLATOR					
Vo	Output voltage	14 ≤ REG_IN ≤ 40 V, 0 ≤ I _O ≤ 20 mA	10	11.5	13	V
	Output voltage in dropout	I _O = 10 mA, REG_IN = 10 V	9	9.6		V
SUPP	PLY CURRENT				•	
I _{CC}	Supply current into V _{CC}	Inputs high or low		0.2	5	μΑ
	Supply current into REG_IN	REG_IN = 20 V, REG_OUT open		40	100	μΑ

⁽¹⁾ Typical values are at $T_A = 25$ °C unless otherwise noted.

⁽²⁾ All voltages are with respect to device GND pin.

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SWITCHING CHARACTERISTICS

over recommended operating ambient temperature range, REG_IN open, $C_L = 1$ nF (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN TYP ⁽¹⁾	MAX	UNIT	
		V _{CC} = 14 V	14	25		
t _r	Rise time	V _{CC} = 10 V	15	30	ns	
		V _{CC} = 5 V	20	35		
		V _{CC} = 14 V	15	25		
t _f	Fall time	V _{CC} = 10 V	15	30	ns	
		V _{CC} = 5 V	18	35		
	Propagation delay time, high-to-low-level output	V _{CC} = 14 V	25	40		
t_{PHL}		V _{CC} = 10 V	25	45	ns	
		V _{CC} = 5 V	34	50		
		V _{CC} = 14 V	24	40		
t _{PLH}	Propagation delay time low-to-high-level output	V _{CC} = 10 V	26	45	ns	
		V _{CC} = 5 V	36	50		

⁽¹⁾ Typical values are at $T_A = 25^{\circ}C$ unless otherwise noted.

PARAMETER MEASUREMENT INFORMATION

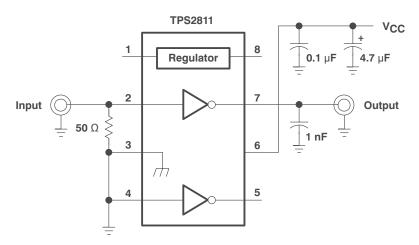


Figure 1. Test Circuit For Measurement of Switching Characteristics

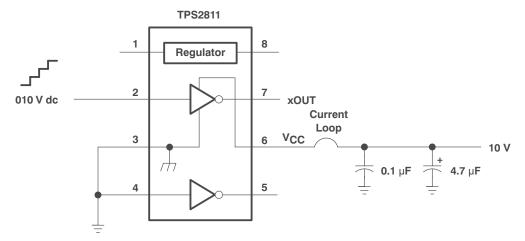


Figure 2. Shoot-Through Current Test Setup

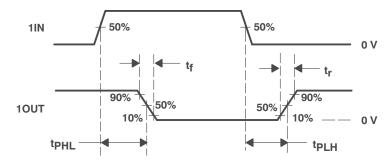


Figure 3. Typical Timing Diagram

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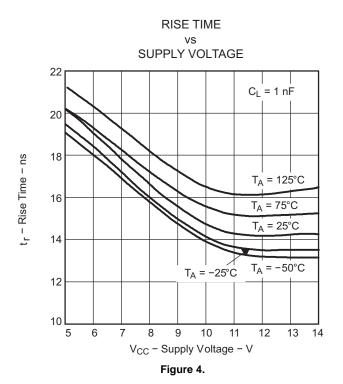


TYPICAL CHARACTERISTICS

Table 1. Characteristics Graphs and Application Information

PARAMETER		vs PARAMETER 2	FIGURE
Typical Characteristics			
Rise time	Supply v	voltage	4
Fall time	Supply v	voltage	5
Propagation delay time	Supply v	voltage	6, 7
		voltage	8
Supply current	Load ca	pacitance	9
	Ambient	temperature	0
Input threshold voltage	Supply v	voltage	11
Regulator output voltage	Regulate	or input voltage	12, 13
Regulator quiescent current	Regulate	or input voltage	14
Peak source current	Supply v	voltage	15
Peak sink current	Supply \	voltage	16
	Input vo	Itage, high-to-low	17
Shoot-through current	Input vo	Itage, low-to-high	18
General Applications	*		·
Switching test circuits and application information			19, 20
N. II. CAOLIT COLIT		Low-to-high	21, 22, 23
Voltage of 10UT vs 20UT	Time	High-to-low	24, 25, 26
Circuit for Measuring Paralleled Switching Characteristic	cs		<u> </u>
Switching test circuits and application information			27
		Low-to-high	28, 30
Input voltage vs output voltage	Time	High-to-low	29, 31
Hex-1 to Hex-4 Application Information			
Driving test circuit and application information			32
		Hex-1 size	33
		Hex-2 size	36
Drain-source voltage vs drain current	Time	Hex-3 size	39
		Hex-4 size	41
		Hex-4 size parallel drive	45
		Hex-1 size	34
		Hex-2 size	37
	Time	Hex-3 size	40
		Hex-4 size	43
		Hex-4 size parallel drive	46
		Hex-1 size	35
		Hex-2 size	38
	Time	Hex-3 size	42
		Hex-4 size	44
		Hex-4 size parallel drive	47
Synchronous Buck Regulator Application		<u> </u>	
3.3-V 3-A Synchronous-Rectified Buck Regulator Circuit			48
Q1 drain voltage vs gate voltage at turn-on	Time		49
Q1 drain voltage vs gate voltage at turn-off	Time		50
Q1 drain voltage vs Q2 gate-source voltage	Time		51, 52, 53
		3 A	54
Output ripple voltage vs inductor current	Time		Ţ.





PROPAGATION DELAY TIME, HIGH-TO-LOW-LEVEL OUTPUT

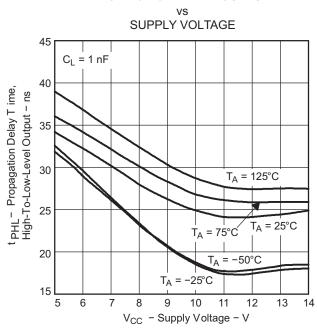
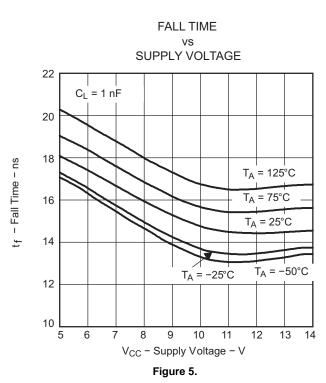


Figure 6.



PROPAGATION DELAY TIME, LOW-TO-HIGH-LEVEL OUTPUT

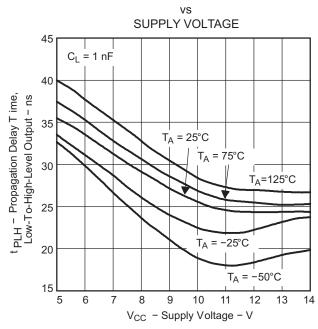
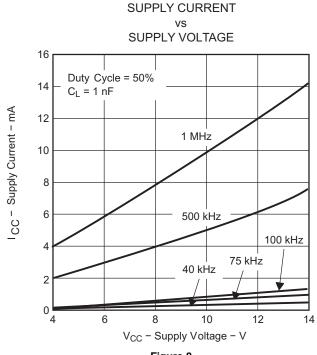


Figure 7.





LOAD CAPACITANCE

2.5

V_{CC} = 10 V

f = 100 kHz

T_A = 25°C

1.5

0

0

0.5

1 1.5

2

C_L - Load Capacitance - nF

SUPPLY CURRENT

Figure 8.

SUPPLY CURRENT ٧S AMBIENT TEMPERATURE 1.2 $C_L = 1 nF$ 1.19 V_{CC} = 10 V Duty Cycle = 50% 1.18 f = 100 kHz I_{CC} - Supply Current - mA 1.17 1.16 1.15 1.14 1.13 1.12 1.11 1.1

25

50

 T_A – Temperature – °C

Figure 10.

75

100

125

INPUT THRESHOLD VOLTAGE vs SUPPLY VOLTAGE

Figure 9.

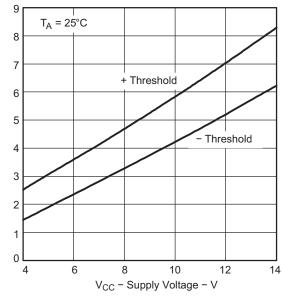


Figure 11.

-50

-25

0

V_{IT} - Input Threshold Voltage - V



Regulator Output Voltage - V

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REGULATOR OUTPUT VOLTAGE

REGULATOR INPUT VOLTAGE

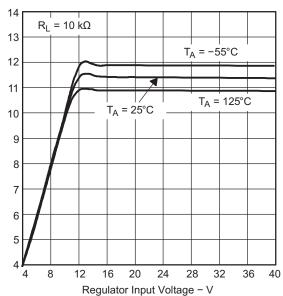


Figure 12.

REGULATOR QUIESCENT CURRENT

REGULATOR INPUT VOLTAGE

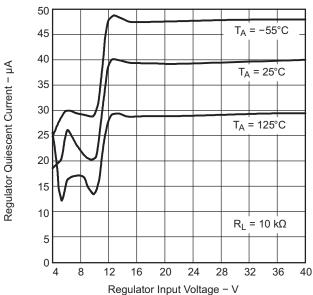


Figure 14.

REGULATOR OUTPUT VOLTAGE REGULATOR INPUT VOLTAGE

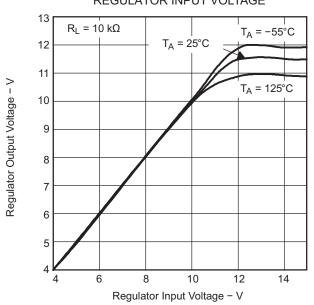


Figure 13.

PEAK SOURCE CURRENT



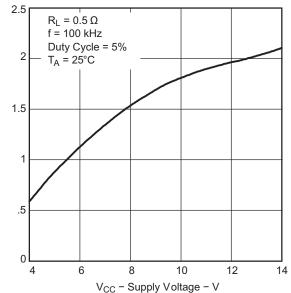


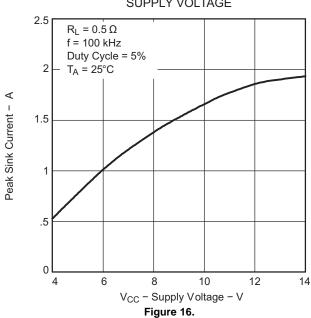
Figure 15.

⋖

Peak Source Current -







SHOOT-THROUGH CURRENT

INPUT VOLTAGE, HIGH-TO-LOW

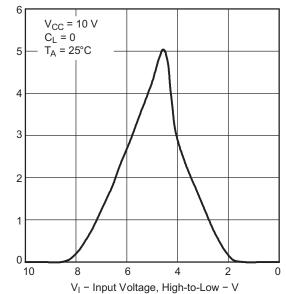


Figure 17.

SHOOT-THROUGH CURRENT

INPUT VOLTAGE, LOW-TO-HIGH

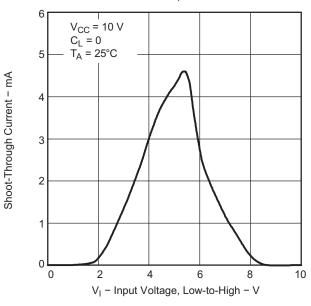


Figure 18.

Shoot-Through Current - mA



APPLICATION INFORMATION

The TPS2811 circuits each contain one regulator and two MOSFET drivers. The regulator can be used to limit V_{CC} to between 10 V and 13 V for a range of input voltages from 14 V to 40 V, while providing up to 20 mA of dc drive. The TPS2811 has inverting drivers. These MOSFET drivers are capable of supplying up to 2.1 A or sinking up to 1.9 A (see Figures 15 and 16) of instantaneous current to n-channel or p-channel MOSFETs. The TPS2811 MOSFET drivers have very fast switching times combined with very short propagation delays. These features enhance the operation of today's high-frequency circuits.

The CMOS input circuit has a positive threshold of approximately 2/3 of V_{CC} , with a negative threshold of 1/3 of V_{CC} , and a very high input impedance in the range of 109Ω . Noise immunity is also very high because of the Schmitt-trigger switching. In addition, the design is such that the normal shoot-through current in CMOS (when the input is biased halfway between V_{CC} and ground) is limited to less than 6 mA. The limited shoot-through is evident in the graphs in Figures 17 and 18. The input stage shown in the functional block diagram better illustrates the way the front end works. The circuitry of the device is such that regardless of the rise and/or fall time of the input signal, the output signal will always have a fast transition speed; this basically isolates the waveforms at the input from the output. Therefore, the specified switching times are not affected by the slopes of the input waveforms.

The basic driver portion of the circuits operate over a supply voltage range of 4 V to 14 V with a maximum bias current of 5 μ A. Each driver consists of a CMOS input and a buffered output with a 2-A instantaneous drive capability. They have propagation delays of less than 30 ns and rise and fall times of less than 20 ns each. Placing a 0.1- μ F ceramic capacitor between V_{CC} and ground is recommended; this will supply the instantaneous current needed by the fast switching and high current surges of the driver when it is driving a MOSFET.

The output circuit is also shown in the functional block diagram. This driver uses a unique combination of a bipolar transistor in parallel with a MOSFET for the ability to swing from VCC to ground while providing 2 A of instantaneous driver current. This unique parallel combination of bipolar and MOSFET output transistors provides the drive required at V_{CC} and ground to guarantee turn-off of even low-threshold MOSFETs. Typical bipolar-only output devices don't easily approach V_{CC} or ground.

The regulator included in the TPS2811 has an input voltage range of 14 V to 40 V. It produces an output voltage of 10 V to 13 V and is capable of supplying from 0 to 20 mA of output current. In grounded source applications, this extends the overall circuit operation to 40 V by clamping the driver supply voltage (V_{CC}) to a safe level for both the driver and the MOSFET gate. The bias current for full operation is a maximum of 150 μ A. A 0.1- μ F capacitor connected between the regulator output and ground is required to ensure stability. For transient response, an additional 4.7- μ F electrolytic capacitor on the output and a 0.1- μ F ceramic capacitor on the input will optimize the performance of this circuit. When the regulator is not in use, it can be left open at both the input and the output, or the input can be shorted to the output and tied to either the V_{CC} or the ground pin of the chip.

Product Folder Link(s): TPS2811-Q1



Matching and Paralleling Connections

Figure 19 and Figure 20 show the delays for the rise and fall time of each channel. As can be seen on a 5-ns scale, there is very little difference between the two channels at no load. Figures 23 and 24 show the difference between the two channels for a 1-nF load on each output. There is a slight delay on the rising edge, but little or no delay on the falling edge. As an example of extreme overload, Figures 25 and 26 show the difference between the two channels, or two drivers in the package, each driving a 10-nF load. As would be expected, the rise and fall times are significantly slowed down. Figures 28 and 29 show the effect of paralleling the two channels and driving a 1-nF load. A noticeable improvement is evident in the rise and fall times of the output waveforms. Finally, Figures 30 and 31 show the two drivers being paralleled to drive the 10-nF load and as could be expected the waveforms are improved. In summary, the paralleling of the two drivers in a package enhances the capability of the drivers to handle a larger load. Because of manufacturing tolerances, it is not recommended to parallel drivers that are not in the same package.

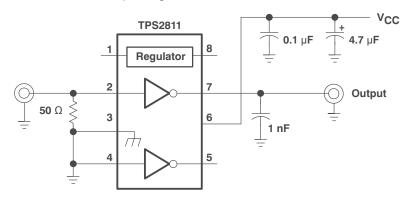
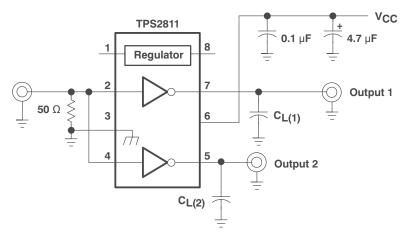


Figure 19. Test Circuit for Measuring Switching Characteristics



A. Input rise and fall times should be ≤10 ns for accurate measurement of ac parameters.

Figure 20. Test Circuit for Measuring Switching Characteristics With the Inputs Connected in Parallel



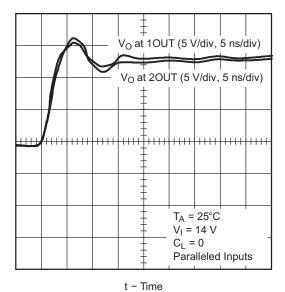


Figure 21. Voltage of 10UT vs Voltage at 20UT, Low-to-High Output Delay

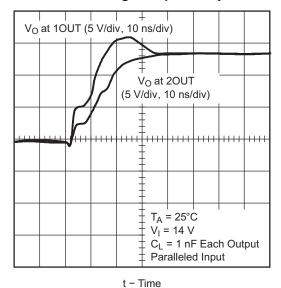


Figure 23. Voltage at 10UT vs Voltage at 20UT, Low-to-High Output Delay

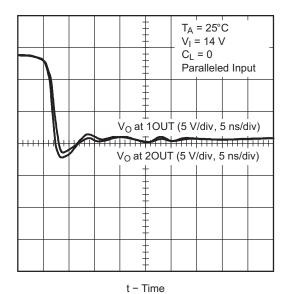


Figure 22. Voltage at 10UT vs Voltage at 20UT, High-to-Low Output Delay

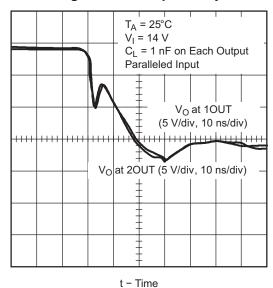
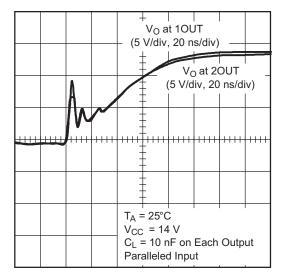


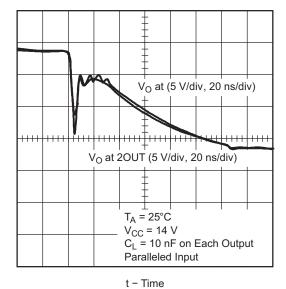
Figure 24. Voltage at 10UT vs Voltage at 20UT, **High-to-Low Output Delay**

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t - Time

Figure 25. Voltage at 10UT vs Voltage at 20UT, Low-to-High Output Delay

Figure 26. Voltage at 10UT vs Voltage at 20UT, High-to-Low Output Delay

A. Input rise and fall times should be ≤10 ns for accurate measurement of ac parameters.

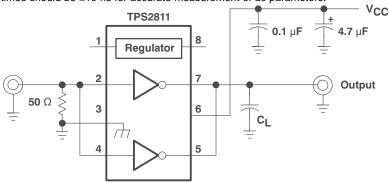


Figure 27. Test Circuit for Measuring Paralleled Switching Characteristics



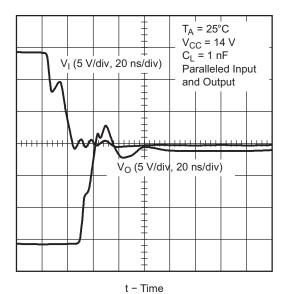


Figure 28. Input Voltage vs Output Voltage, Low-to-High Propagation Delay of Paralleled Drivers

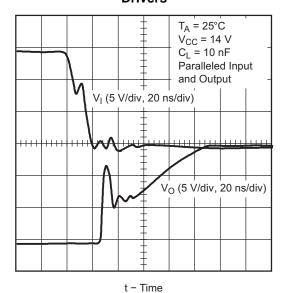


Figure 30. Input Voltage vs Output Voltage, Low-to-High Propagation Delay of Paralleled Drivers

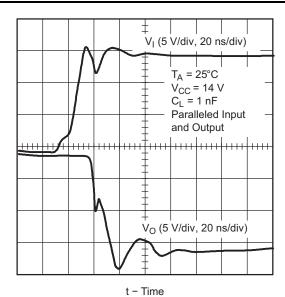


Figure 29. Input Voltage vs Output Voltage, High-to-Low Propagation Delay of Paralleled Drivers

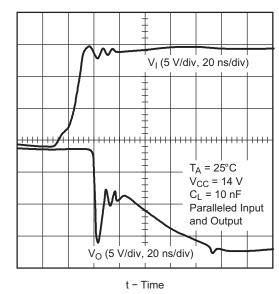


Figure 31. Input Voltage vs Output Voltage, High-to-Low Propagation Delay of Paralleled Drivers

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Figures 33 through 47 illustrate the performance of the TPS2811 driving MOSFETs with clamped inductive loads, similar to what is encountered in discontinuous-mode flyback converters. The MOSFETs that were tested range in size from Hex-1 to Hex-4, although the TPS28xx family is only recommended for Hex-3 or below.

The test circuit is shown in Figure 32. The layout rules observed in building the test circuit also apply to real applications. Decoupling capacitor C1 is a 0.1- μ F ceramic device, connected between V_{CC} and GND of the TPS2811, with short lead lengths. The connection between the driver output and the MOSFET gate, and between GND and the MOSFET source, are as short as possible to minimize inductance. Ideally, GND of the driver is connected directly to the MOSFET source. The tests were conducted with the pulse generator frequency set very low to eliminate the need for heat sinking, and the duty cycle was set to turn off the MOSFET when the drain current reached 50% of its rated value. The input voltage was adjusted to clamp the drain voltage at 80% of its rating.

As shown, the driver is capable of driving each of the Hex-1 through Hex-3 MOSFETs to switch in 20 ns or less. Even the Hex-4 is turned on in less than 20 ns. Figures 45, 46 and 47 show that paralleling the two drivers in a package enhances the gate waveforms and improves the switching speed of the MOSFET. Generally, one driver is capable of driving up to a Hex-4 size. The TPS2811 family is even capable of driving large MOSFETs that have a low gate charge.

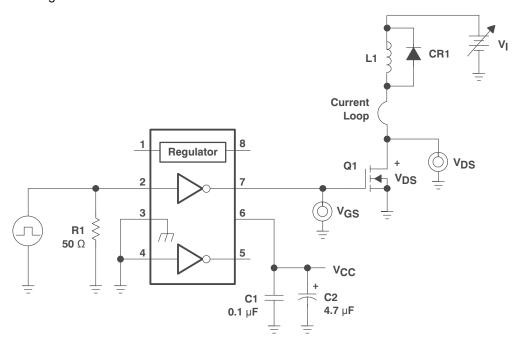


Figure 32. TPS2811 Driving Hex-1 through Hex-4 Devices



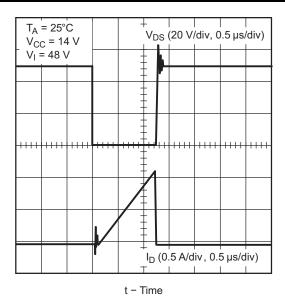


Figure 33. Drain-Source Voltage vs Drain Current, TPS2811 Driving an IRFD014 (Hex-1 Size)

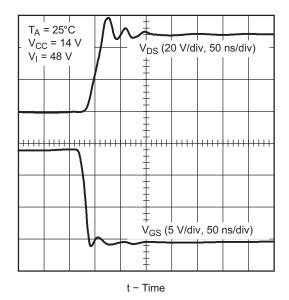


Figure 35. Drain-Source Voltage vs Gate-Source Voltage, at Turn-off, TPS2811 Driving an IRFD014 (Hex-1 Size)

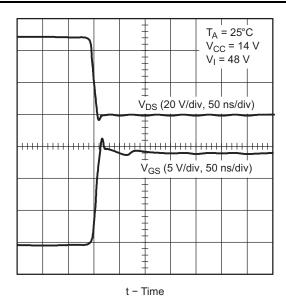


Figure 34. Drain-Source Voltage vs Gate-Source Voltage, at Turn-on, TPS2811 Driving an IRFD014

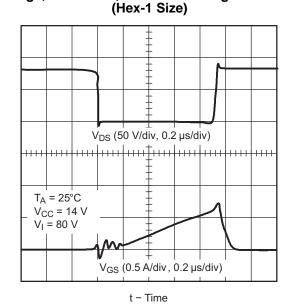


Figure 36. Drain-Source Voltage vs Drain Current, TPS2811 Driving an IRFD120 (Hex-2 Size)

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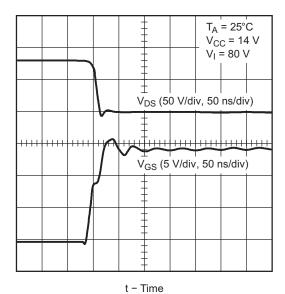


Figure 37. Drain-Source Voltage vs Gate-Source Voltage, at Turn-on, TPS2811 Driving an IRFD120 (Hex-2 Size)

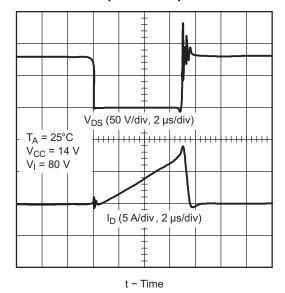
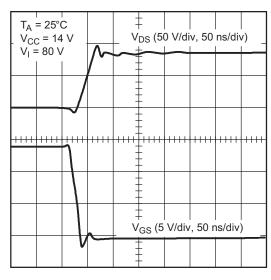
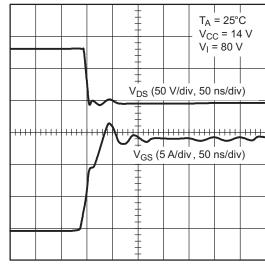


Figure 39. Drain-Source Voltage vs Drain Current, TPS2811 Driving an IRF530 (Hex-3 Size)



t - Time

Figure 38. Drain-Source Voltage vs Gate-Source Voltage, at Turn-off, TPS2811 Driving an IRFD120 (Hex-2 Size)



t - Time

Figure 40. Drain-Source Voltage vs Gate-Source Voltage, at Turn-on, TPS2811 Driving an IRF530 (Hex-3 Size)



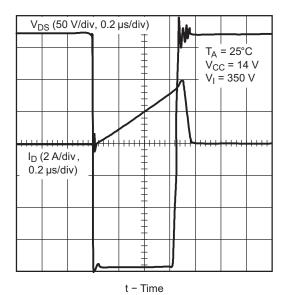


Figure 41. Drain-Source Voltage vs Drain Current, One Driver, TPS2811 Driving an IRF840 (Hex-4 Size)

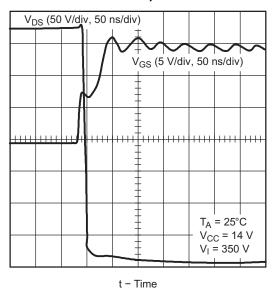


Figure 43. Drain-Source Voltage vs Gate-Source Voltage, at Turn-on, One Driver, TPS2811 Driving an IRF840 (Hex-4 Size)

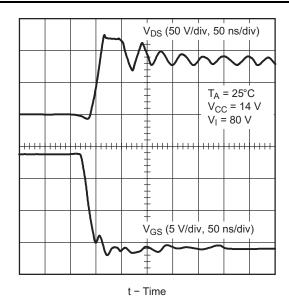


Figure 42. Drain-Source Voltage vs Gate-Source Voltage, at Turn-off, TPS2811 Driving an IRF530 (Hex-3 Size)

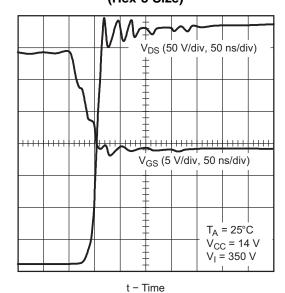
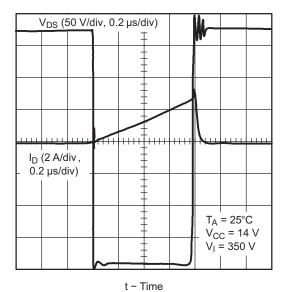


Figure 44. Drain-Source Voltage vs Gate-Source Voltage, at Turn-off, One Driver, TPS2811 Driving an IRF840 (Hex-4 Size)

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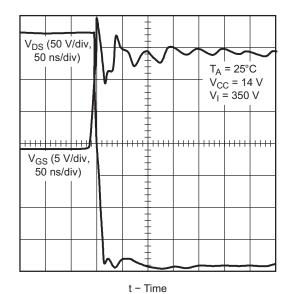


Figure 45. Drain-Source Voltage vs Drain Current, Parallel Drivers, TPS2811 Driving an IRF840 (Hex-4 Size)

Figure 46. Drain-Source Voltage vs Gate-Source Voltage, at Turn-on, Parallel Drivers, TPS2811 Driving an IRF840 (Hex-4 Size)

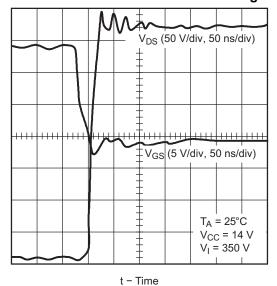


Figure 47. Drain-Source Voltage vs Gate-Source Voltage, at Turn-off, Parallel Drivers, TPS2811 Driving an IRF840 (Hex-4 Size)

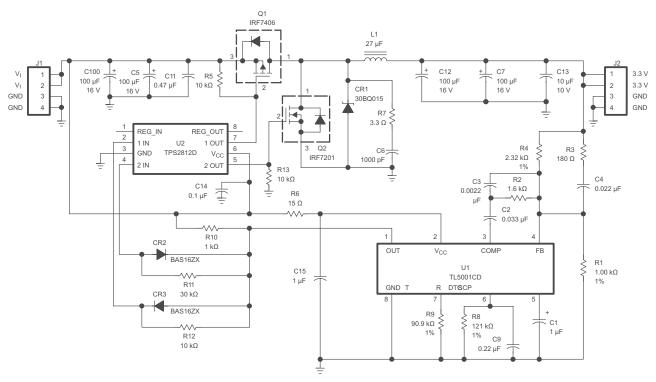
20

Product Folder Link(s): TPS2811-Q1

Synchronous Buck Regulator

Figure 48 is the schematic for a 100-kHz synchronous-rectified buck converter implemented with a TL5001 pulse-width-modulation (PWM) controller and a TPS2812 driver. The bill of materials is provided in Table 1. The converter operates over an input range from 5.5 V to 12 V and has a 3.3-V output capable of supplying 3 A continuously and 5 A during load surges. The converter achieves an efficiency of 90.6% at 3 A and 87.6% at 5 A. Figures 49 and 50 show the power switch switching performance. The output ripple voltage waveforms are documented in Figures 54 and 55.

The TPS2812 drives both the power switch, Q2, and the synchronous rectifier, Q1. Large shoot-through currents, caused by power switch and synchronous rectifier remaining on simultaneously during the transitions, are prevented by small delays built into the drive signals, using CR2, CR3, R11, R12, and the input capacitance of the TPS2812. These delays allow the power switch to turn off before the synchronous rectifier turns on and vice versa. Figure 51 shows the delay between the drain of Q2 and the gate of Q1; expanded views are provided in Figures 52 and 53.



NOTE: If the parasitics of the external circuit cause the voltage to violate the Absolute Maximum Rating for the Output pins, Schottky diodes should be added from ground to output and from output to V_{CC}.

Figure 48. 3.3-V 3-A Synchronous-Rectified Buck Regulator Circuit

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Table 2. Bill of Materials, 3.3-V, 3-A Synchronous-Rectified Buck Converter⁽¹⁾

REFERENCE	DESCRIPTION	DESCRIPTION VENDOR		
U1	TL5001CD, PWM	Texas Instruments	972-644-5580	
U2	TPS2812D, N.I. MOSFET Driver	Texas Instruments	972-644-5580	
CR1	3 A, 15 V, Schottky, 30BQ015	International Rectifier	310-322-3331	
CR2,CR3	Signal Diode, BAS16ZX	Zetex	516-543-7100	
C1	1 μF, 16 V, Tantalum			
C2	0.033 μF, 50 V			
C3	0.0022 μF, 50 V			
C4	0.022 μF, 50 V			
C5,C7,C10,C12	100 μF, 16 V, Tantalum, TPSE107M016R0100	AVX	800-448-9411	
C6	1000 pF, 50 V			
C9	0.22 μF, 50 V			
C11	0.47 μF, 50 V, Z5U			
C13	10 μF, 10 V, Ceramic, CC1210CY5V106Z	TDK	708-803-6100	
C14	0.1 μF, 50 V			
C15	1.0 μF, 50 V			
J1,J2	4-Pin Header	Nova Magnetics, Inc.	972-272-8287	
L1	27 μH, 3 A/5 A, SML5040	International Rectifier	310-322-3331	
Q1	IRF7406, P-FET	International Rectifier	310-322-3331	
Q2	IRF7201, N-FET			
R1	1.00 kΩ, 1%			
R2	1.6 kΩ			
R3	180 Ω			
R4	2.32 kΩ, 1 %			
R5,R12,R13	10 kΩ			
R6	15 Ω			
R7	3.3 Ω			
R8	121 kΩ, 1%			
R9	90.9 kΩ, 1%			
R10	1 kΩ			
R11	30 kΩ			

⁽¹⁾ Unless otherwise specified, capacitors are X7R ceramics, and resistors are 5%, 1/10 W.

Product Folder Link(s): TPS2811-Q1



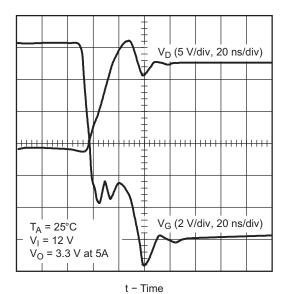


Figure 49. Q1 Drain Voltage vs Gate Voltage, at Switch Turn-on

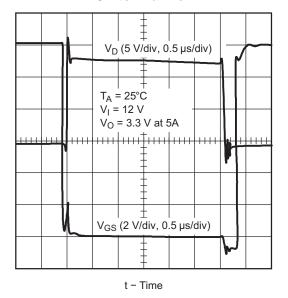


Figure 51. Q1 Drain Voltage vs Q2 Gate-Source Voltage

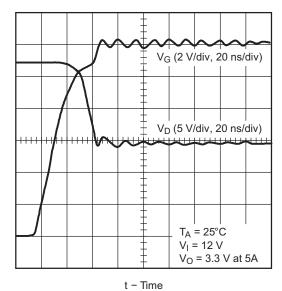


Figure 50. Q1 Drain Voltage vs Gate Voltage, at Switch Turn-off

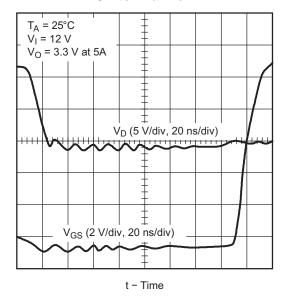


Figure 52. Q1 Drain Voltage vs Q2 Gate-Source Voltage

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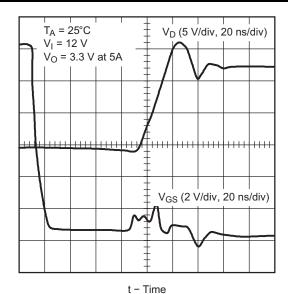


Figure 53. Q1 Drain Voltage vs Q2 Gate-Source Voltage

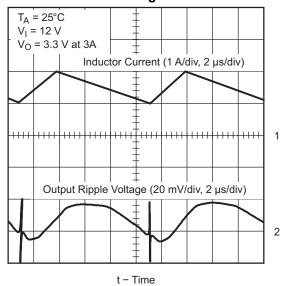


Figure 54. Output Ripple Voltage vs Inductor Current, at 3 A

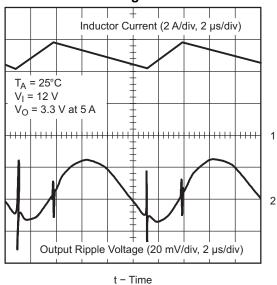


Figure 55. Output Ripple Voltage vs Inductor Current, at 5 A



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PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing		Package Qty	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Top-Side Markings	Samples
TPS2811QPWRQ1	ACTIVE	TSSOP	PW	8	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR	-40 to 125	2811Q	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ Only one of markings shown within the brackets will appear on the physical device.

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OTHER QUALIFIED VERSIONS OF TPS2811-Q1:

Catalog: TPS2811

NOTE: Qualified Version Definitions:





24-Jan-2013

• Catalog - TI's standard catalog product

PW (R-PDSO-G8)

PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M—1994.
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.
- E. Falls within JEDEC MO-153



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